

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

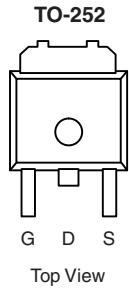
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
60	0.026 at $V_{GS} = 10$ V	45
	0.029 at $V_{GS} = 4.5$ V	40

FEATURES

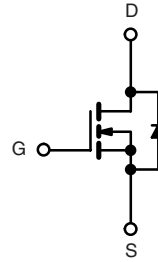
- Trench Power MOSFET
- 175 °C Junction Temperature



Available
RoHS*
 COMPLIANT



Drain Connected to Tab



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175$ °C) ^b	$T_C = 25$ °C	I_D	40	A
	$T_C = 100$ °C		35	
Pulsed Drain Current		I_{DM}	100	
Continuous Source Current (Diode Conduction)		I_S	23	
Avalanche Current		I_{AS}	20	mJ
Single Avalanche Energy (Duty Cycle ≤ 1 %)	$L = 0.1$ mH	E_{AS}	20	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	100	W
	$T_A = 25$ °C		3 ^a	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	18	22	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	3.2	4	

Notes:

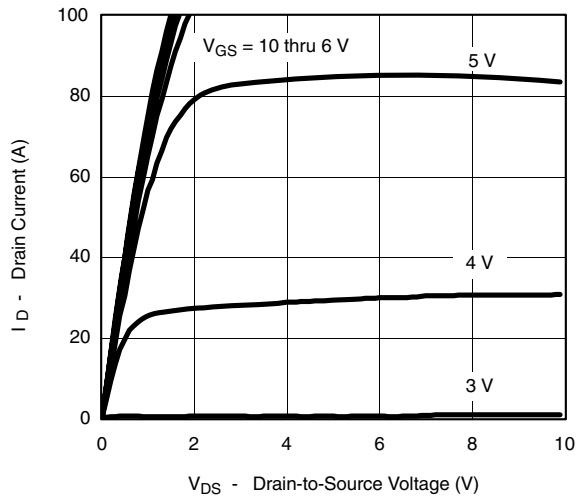
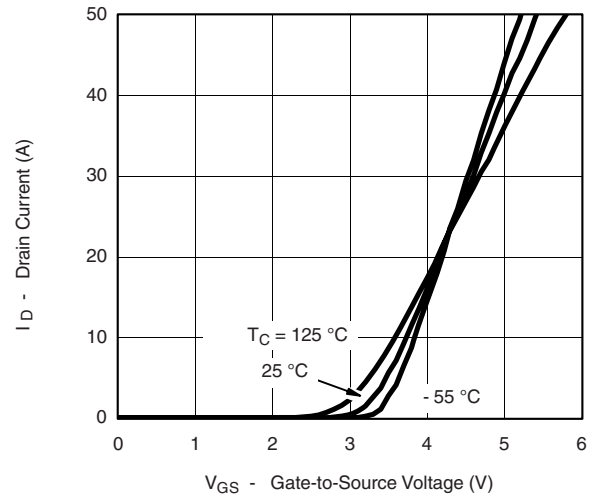
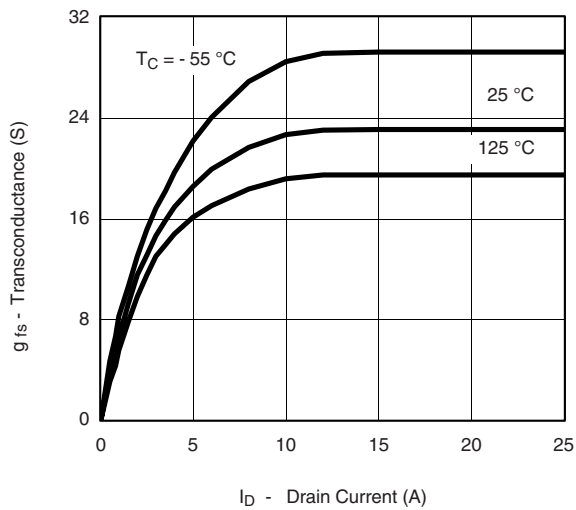
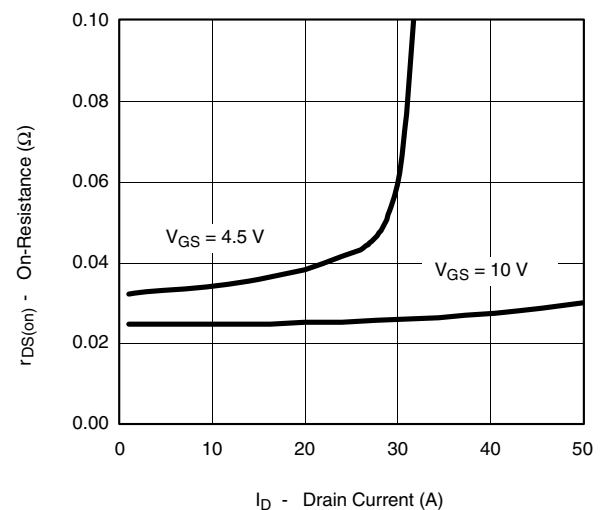
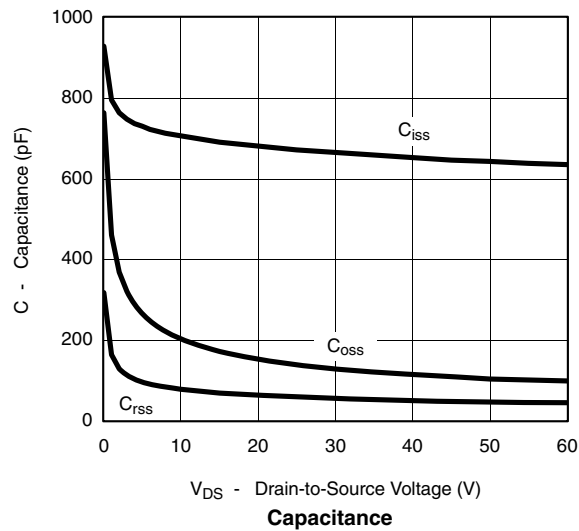
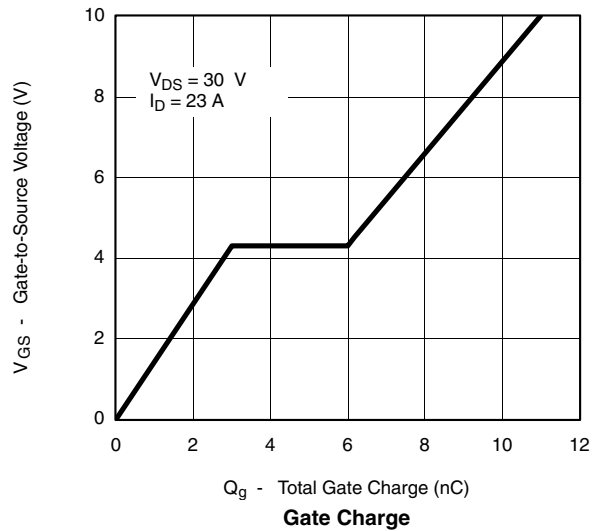
a. Surface Mounted on 1" x 1" FR4 board, $t \leq 10$ sec.

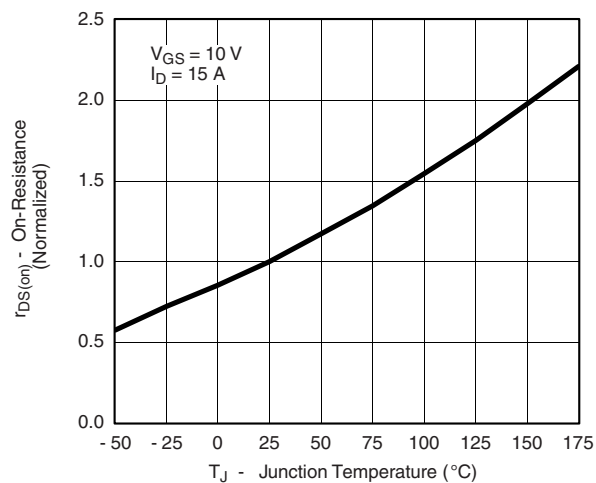
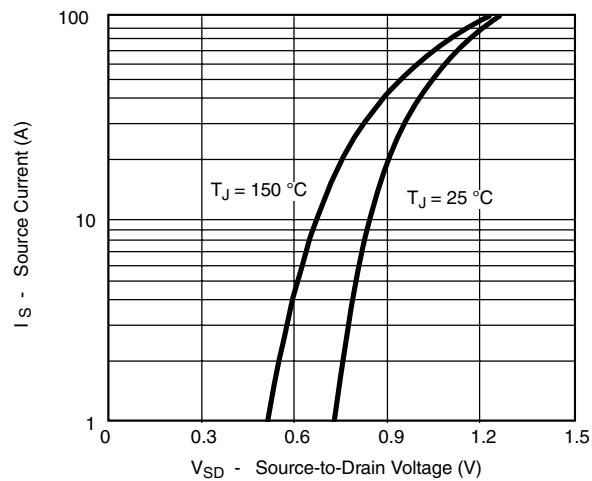
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0	2.0	3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.026		Ω
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.055		
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$		0.069		
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$		0.029		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		20		S
Dynamic ^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		1850		pF
Output Capacitance	C_{oss}			140		
Reverse Transfer Capacitance	C_{rss}			60		
Total Gate Charge ^c	Q_g	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 23\text{ A}$		11	17	nC
Gate-Source Charge ^c	Q_{gs}			3		
Gate-Drain Charge ^c	Q_{gd}			3		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 1.3\text{ }\Omega$ $I_D \cong 23\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		8	15	ns
Rise Time ^c	t_r			15	25	
Turn-Off Delay Time ^c	$t_{d(off)}$			30	45	
Fall Time ^c	t_f			25	40	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^{\circ}\text{C}$)						
Pulsed Current	I_{SM}				50	A
Diode Forward Voltage	V_{SD}	$I_F = 15\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	60	ns

Notes:

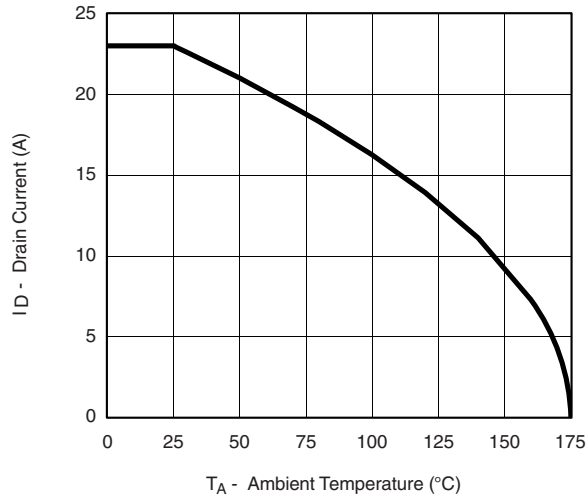
- a. For design aid only; not subject to production testing.
 b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

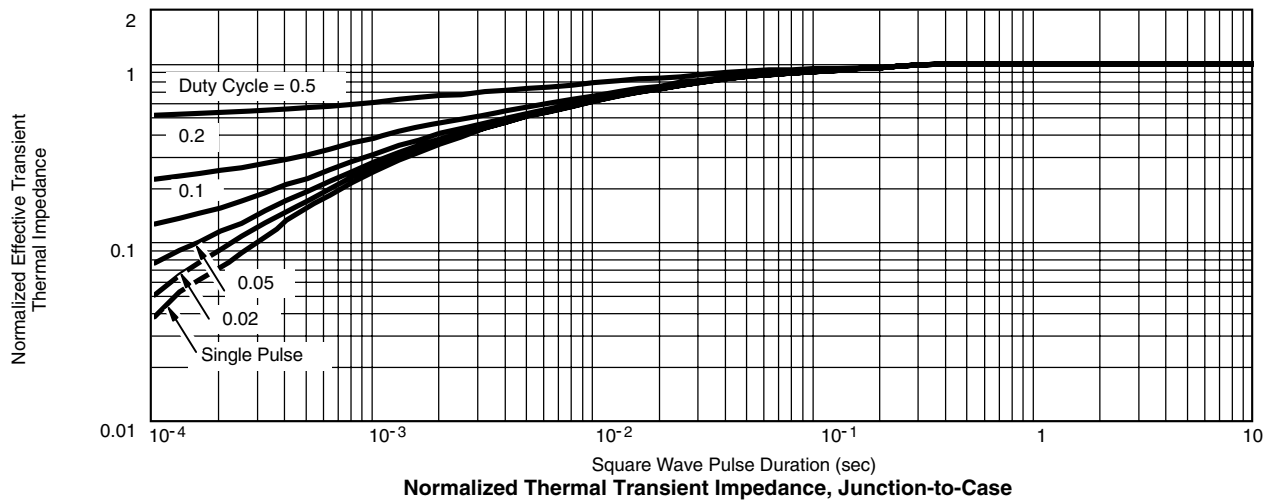
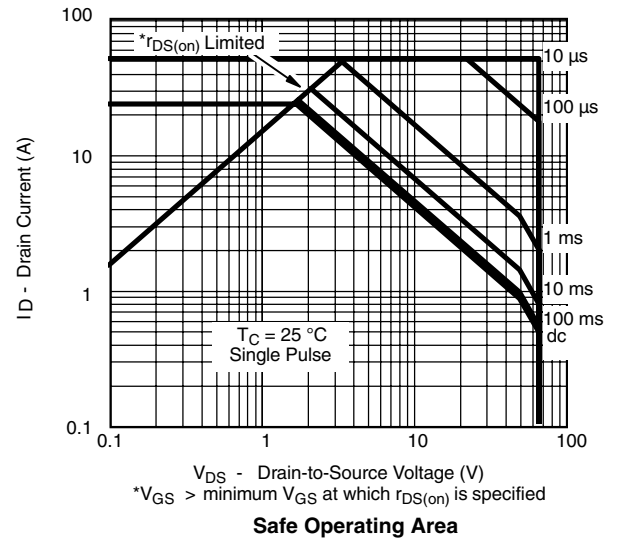
TYPICAL CHARACTERISTICS 25 °C unless noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS 25 °C unless noted**On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage**

THERMAL RATINGS



T_A - Ambient Temperature (°C)
**Maximum Drain Current
 vs. Ambient Temperature**



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